

ABSTRACT OF THE DISCLOSURE

A very thin oxide film is formed on an amorphous silicon film that is formed on a glass substrate, and an aqueous solution such as an acetate solution added with a catalyst element such as nickel by 10 to 5 200 ppm (adjustment needed) is dropped thereon. After the structure is held in this state for a predetermined period, spin drying is performed by using a spinner. A crystalline silicon film is obtained by 10 subjecting the structure to a heat treatment of 550°C and 4 hours and then to laser light irradiation. A crystalline silicon film having a smaller defect concentration is obtained by further performing a heat treatment of 550°C and 4 hours.